# MSKSEMI 美森科













TSS

MOV

GDT

PIFD

2SC5658

**Product specification** 





## **General Description**

This NPN transistor is designed for general purpose amplifier applications. This device is housed in the SOT-723 package which is designed for low power surface mount applications, where board space is at a premium.

# **General Features**

- Reduces Board Space
- High hFE, 210-460 (typical)
- Low VCE(sat), < 0.5 V
- Available in 8 mm, 7-inch/3000 Unit Tape and Reel
- These are Pb-Free Devices

## **Reference News**

PACKAGE OUTLINE	Pin Configuration	Mar	king
WEIGE H	COLLECTOR	BR	BQ
SOT-723	1 2 BASE EMITTER	2SC5658-R-MS	2SC5658-Q-MS



## **MAXIMUM RATINGS(Ta = 25°C)**

Rating	Symbol	Value	Unit
Collector-Base Voltage	V(BR)CBO	50	Vdc
Collector-Emitter Voltage	V(BR)CEO	50	Vdc
Emitter-Base Voltage	V(BR)EBO	5.0	Vdc
Collector Current - Continuous	lc	100	mAdc

#### THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation (Note 1)	Po	260	W
Junction Temperature	TJ	150	°C
Storage Temperature Range	Tstg	- 55 ~ + 150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

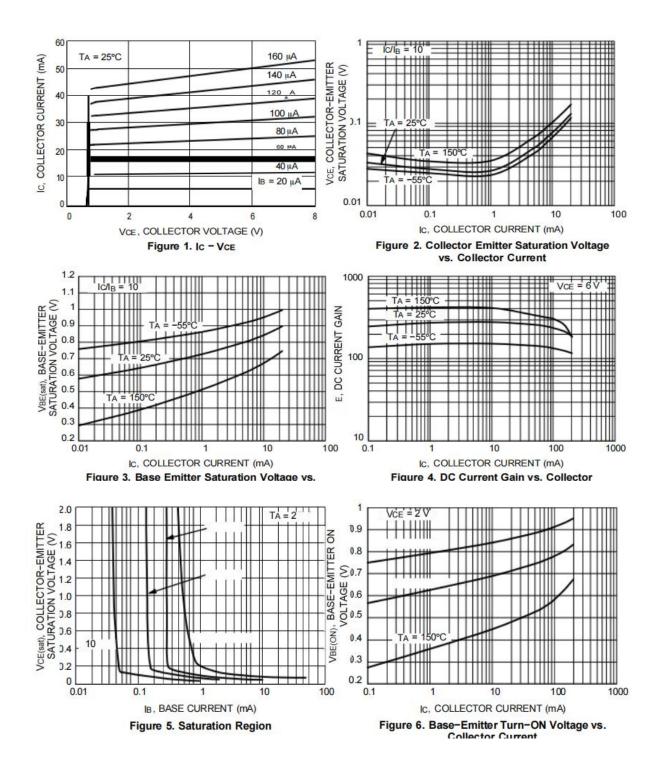
## **ELECTRICAL CHARACTERISTICS** (TA = 25°C)

Characteristic	Symbol	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage (I <sub>C</sub> = 50 µAdc, I <sub>E</sub> = 0)	V(BR)CBO	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Ic = 1.0 mAdc, IB = 0)	V(BR)CEO	50	-	-	Vdc
Emitter-Base Breakdown Voltage (IE = 50	V(BR)EBO	5.0	-	-	Vdc
Collector-Base Cutoff Current (VCB = 30 Vdc, IE = 0)	Ісво	-	-	0.5	<b>⊩</b> A
Emitter-Base Cutoff Current (VEB = 4.0 Vdc, IB = 0)	<b>І</b> ЕВО	-	-	0.5	<b>μ</b> Α
Collector-Emitter Saturation Voltage (Note 2) (Ic = 50 mAdc, IB = 5.0 mAdc)	VCE(sat)	_	_	0.4	Vdc
DC Current Gain (Note 2)         (VCE = 6.0 Vdc, Ic = 1.0 mAdc)       2SC5658Q         (VCE = 6.0 Vdc, Ic = 1.0 mAdc)       2SC5658R	h <sub>FE</sub>	120 180		270 390	-
Transition Frequency (V <sub>CE</sub> = 12 Vdc, I <sub>C</sub> = 2.0 mAdc, f = 30 MHz)	f <sub>T</sub>	-	180	-	MHz
Output Capacitance (V <sub>CB</sub> = 12 Vdc, Ic = 0 Adc, f = 1.0 MHz)	Сов	-	2.0	-	P <sub>F</sub>

2. Pulse Test: Pulse Width  $\leq$  300 s, D.C.  $\leq$  2%



#### **ELECTRICAL CHARACTERISTICS CURVES**





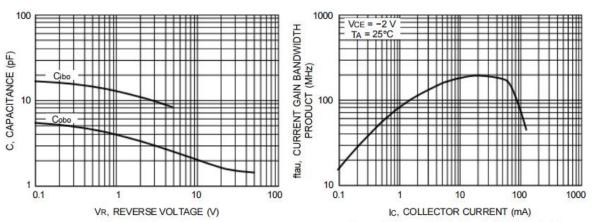


Figure 7. Capacitance

Figure 8. Current Gain Bandwidth Product vs. Collector Current

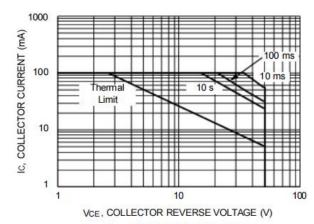
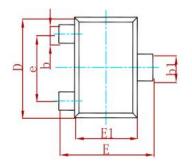
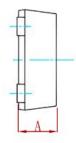


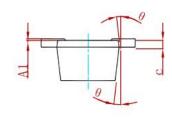
Figure 9. Safe Operating Area



## PACKAGE MECHANICAL DATA

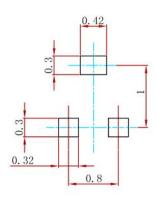






Symbol	Dimensions	In Millimeters	Dimensions	In Inches
Symbol	Min.	Max.	Min.	Max.
Α	0.430	0.500	0.017	0.020
A1	0.000	0.050	0.000	0.002
b	0.170	0.270	0.007	0.011
b1	0.270	0.370	0.011	0.015
С	0.080	0.150	0.003	0.006
D	1.150	1.250	0.045	0.049
E	1.150	1.250	0.045	0.049
E1	0.750	0.850	0.030	0.033
е	0 800	TYP	0 031	ITYP
θ	7° REF.		7° R	REF.

# **Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

## **REEL SPECIFICATION**

P/N	PKG	QTY
2SC5658	SOT-723	8000



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